

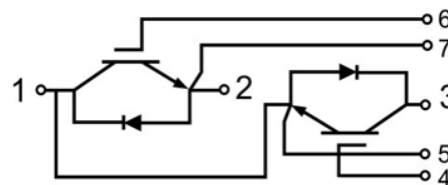
GT75HF120T1VH

Circuit Diagram

IGBT Module

Features:

- $V_{CES}=1200V$ $I_C=75A$ Trench & Field Stop IGBT Module
- Short Circuit Capability
- Low Switching Loss
- 100% RBSOA Tested($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- High Power Converters
- Motor Drives
- UPS Systems

Type	Package	Marking
GT75HF120T1VH	T1V	GT75HF120T1VH

IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current Limited by T_{Jmax}	$T_C=90^\circ C$	75	A
		$T_C=25^\circ C$	150	A
I_{CM}	Peak Collector Current Repetitive	T_p limited by T_{Jmax}	150	A
P_D	Maximum Power Dissipation (IGBT)	$T_C=25^\circ C, T_{Jmax}=175^\circ C$	380	W



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Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{GE(th)}	Gate-Emitter Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}		4.8	5.6	6.4	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =75A, V _{GE} =15V	T _J =25°C		1.68	2.05	V
			T _J =125°C		2.15		V
			T _J =175°C		2.30		V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V, V _{CE} =1200V, T _J =25°C				1	mA
I _{GES}	Gate-Emitter Leakage Current	V _{GE} =20V, V _{CE} =0V, T _J =25°C				200	nA
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=100kHz			7.71		nF
C _{oes}	Output Capacitance				0.42		nF
C _{res}	Reverse Transfer Capacitance				0.08		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_C=75A,$ $R_{Gon}=4.7\Omega, V_{GE}=\pm 15V,$ Inductive Load	$T_J=25^{\circ}C$		112		ns
			$T_J=125^{\circ}C$		119		
			$T_J=175^{\circ}C$		122		
t_r	Rise Time		$T_J=25^{\circ}C$		28		ns
			$T_J=125^{\circ}C$		36		
			$T_J=175^{\circ}C$		40		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^{\circ}C$		204		ns
			$T_J=125^{\circ}C$		233		
			$T_J=175^{\circ}C$		245		
t_f	Fall Time	$T_J=25^{\circ}C$		214		ns	
		$T_J=125^{\circ}C$		282			
		$T_J=175^{\circ}C$		303			
E_{on}	Turn-on Switching Loss	$V_{CC}=600V, I_C=75A,$ $R_{Gon}=4.7\Omega, V_{GE}=\pm 15V,$ $di/dt=1500A/\mu s(T_J=175^{\circ}C)$ Inductive Load	$T_J=25^{\circ}C$		5.2		mJ
		$T_J=125^{\circ}C$		7.4			
		$T_J=175^{\circ}C$		9.1			



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E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =75A, R _{Goff} =4.7Ω, V _{GE} =±15V, du/dt=5300V/μs(T _J =175°C) Inductive Load	T _J =25°C		5.6		mJ
			T _J =125°C		7.2		
			T _J =175°C		8.1		
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C		425		nC
R _{G (int)}	Internal Gate Resistance		T _J =25°C		7.5		Ω
T _{SC}	V _{CC} =600V, V _{GE} =±15V, T _J =175°C note1					10	us
R _{θJC}	IGBT Thermal Resistance: Junction-to-Case (per IGBT)					0.387	°C/W
R _{θCS}	IGBT Thermal Resistance: Case-to-Sink (per IGBT) (per IGBT, λ _{grease} = 1 W/(m · K))				0.094		°C/W

note1: Short circuit withstand time cannot exceed 10us under specified condition

Diode, Inverter

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current		75	A
I _{FM}	Diode Maximum Forward Current	tp=1ms	150	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =75A	T _J =25°C		1.62	1.95	V
			T _J =125°C		1.70		
			T _J =175°C		1.68		
t _{rr}	Reverse Recovery Time	I _F =75A, -diF/dt=2000A/μs(T _J =175°C), V _R =600V, V _{GE} =-15V	T _J =25°C		300		ns
			T _J =125°C		424		
			T _J =175°C		530		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C		77		A
			T _J =125°C		76		
			T _J =175°C		77		
Q _{rr}	Reverse Recovery Charge		T _J =25°C		7.3		μC
			T _J =125°C		12.1		
			T _J =175°C		15.2		



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E _{rec}	Reverse Recovery Energy	I _F =75A, -diF/dt=2000A/μs(T _J =175°C), V _R =600V, V _{GE} =-15V	T _J =25°C		2.7		mJ
			T _J =125°C		4.7		
			T _J =175°C		6.0		
R _{θJC}	Diode Thermal Resistance: Junction-to-Case (per Diode)					0.675	°C/W
R _{θCS}	Diode Thermal Resistance: Case-to-Sink (per Diode, λ _{grease} = 1 W/(m • K))				0.164		°C/W

Module

Symbol	Description		Min.	Typ.	Max.	Units
V_{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 60s	2500			V
T_J	Maximum Junction Temperature		-40		175	$^\circ C$
T_{JOP}	Maximum Operating Junction Temperature Range ^{note2}		-40		150	$^\circ C$
T_{stg}	Storage Temperature		-40		125	$^\circ C$
CTI	Comparative Tracking Index		200			
M	Power Terminals Screw:M5		3.0		5.0	N·m
M	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			165		g

note2: $T_{JOP} > 150^\circ C$ is only allowed for operation at overload conditions.

Ordering Information Table

Device code	G	T	75	HF	120	T1V	H
	①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Field Stop Trench Gate IGBT
- ③ - Rated Current (75=75A)
- ④ - Circuit Configuration (Half Bridge)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)



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IGBT Module Datasheet

Characteristic diagram

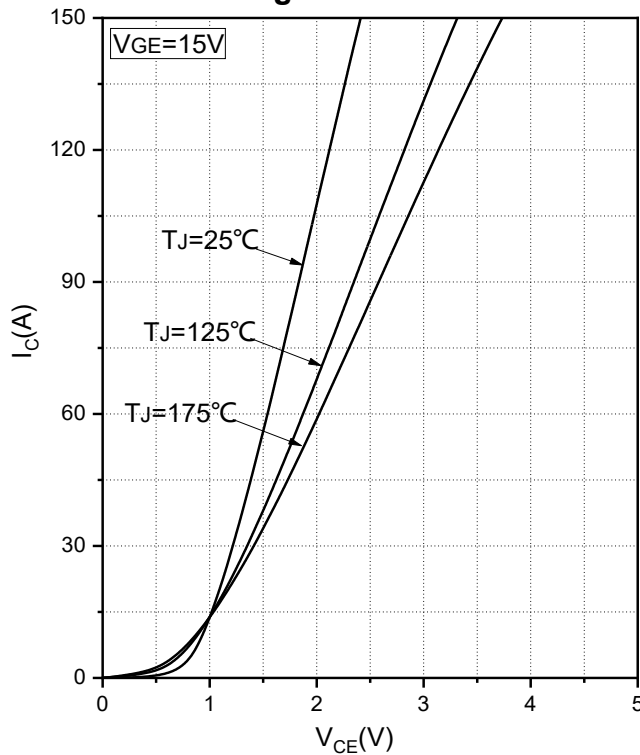


Fig.1 Typical Saturation Voltage Characteristics

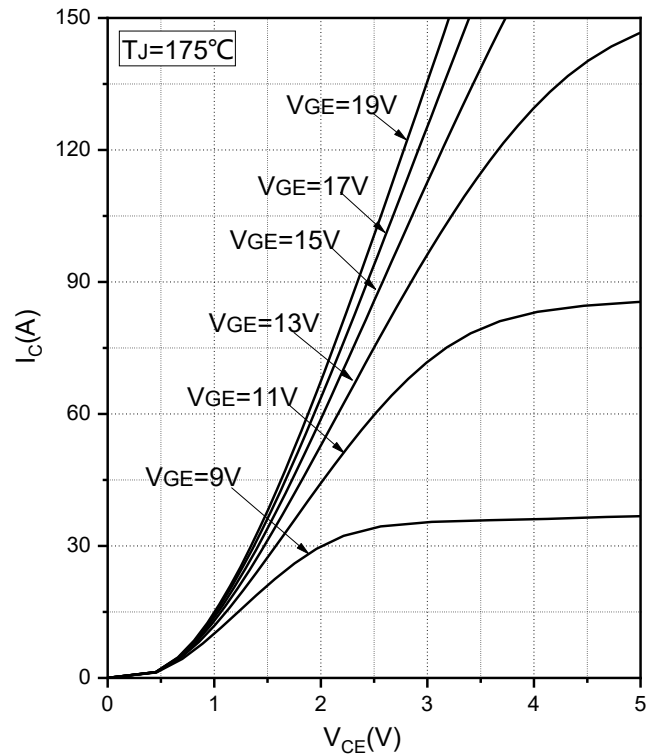


Fig.2 Typical Output Characteristics

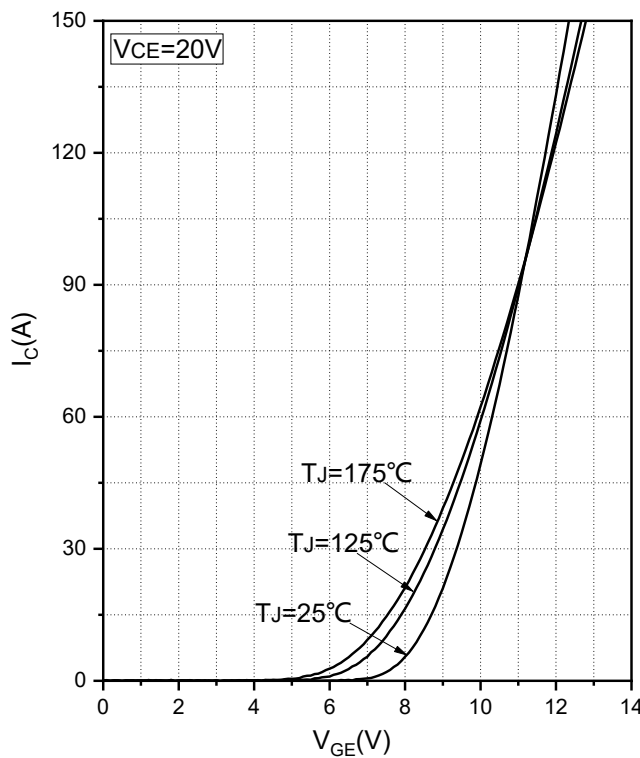


Fig.3 Transfer Characteristic

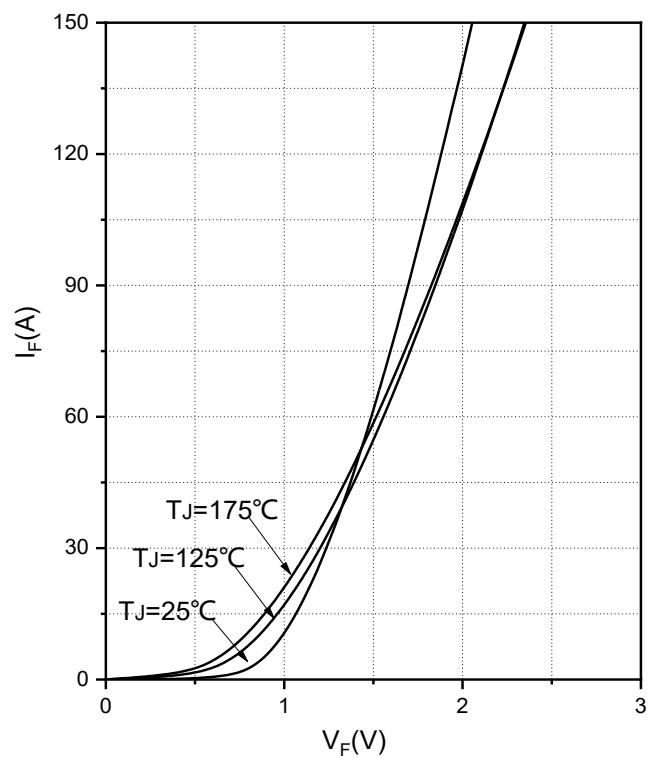


Fig.4 Forward Characteristics of Diode

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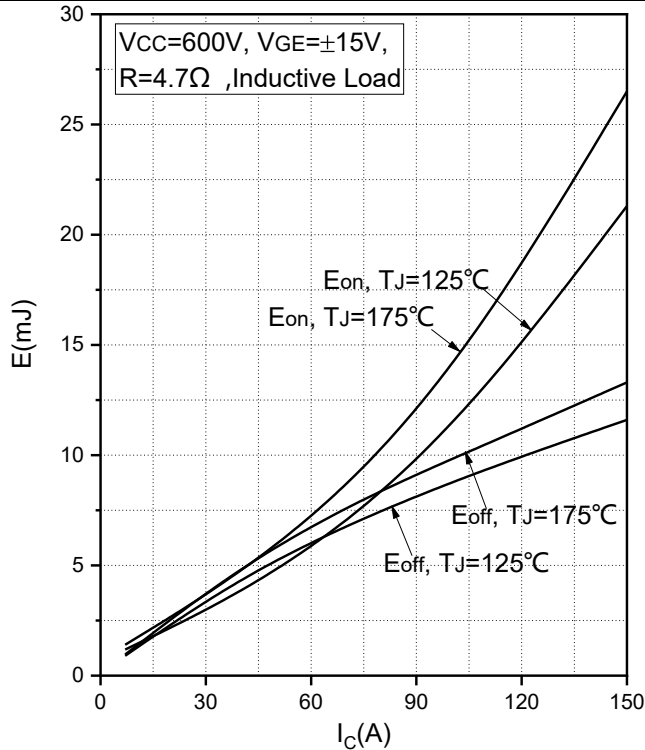


Fig.5 Typical Switching Loss vs. Collector Current

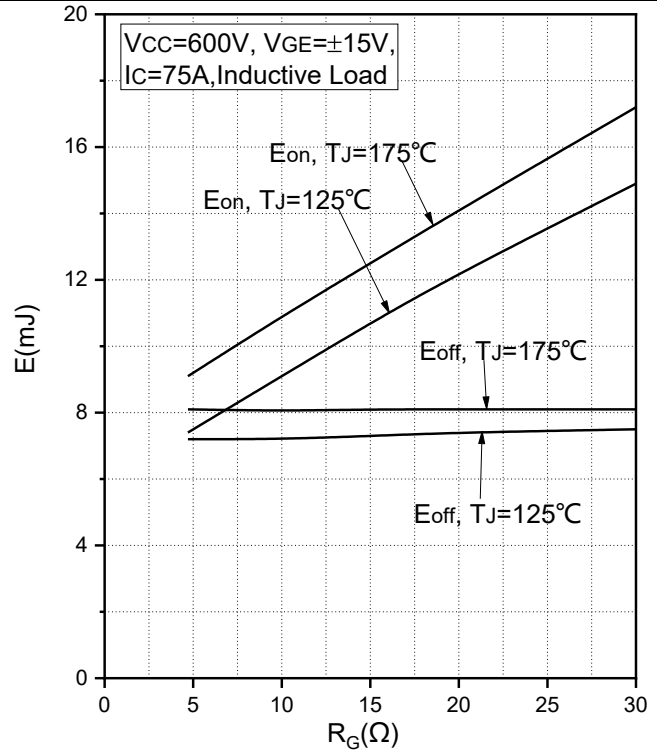


Fig.6 Typical Switching Loss vs. Gate Resistance

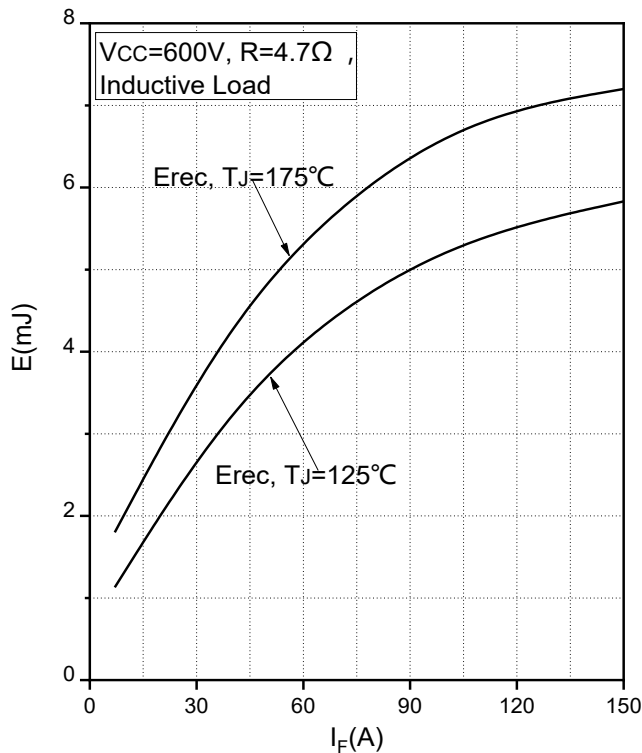


Fig.7 Typical Switching Loss vs. Forward Current

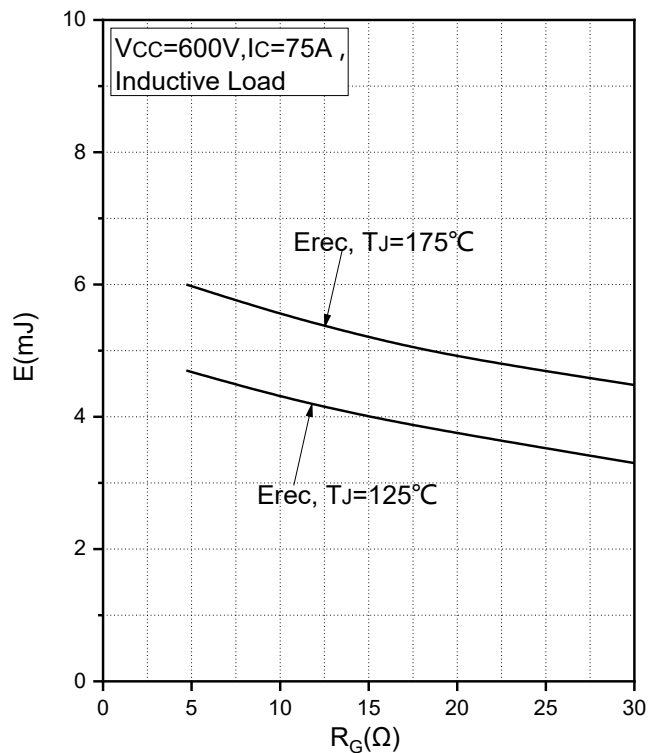


Fig.8 Typical Switching Loss vs. Gate Resistance

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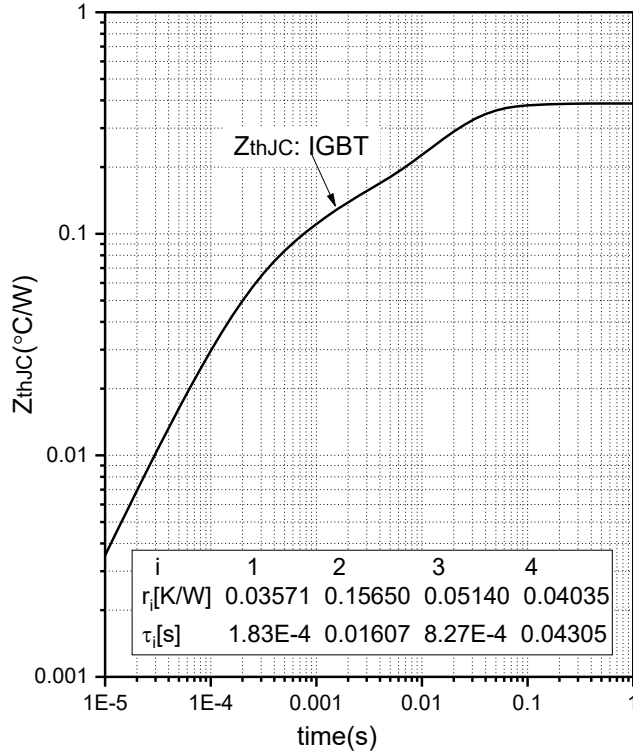


Fig.9 Transient Thermal Impedance (IGBT)

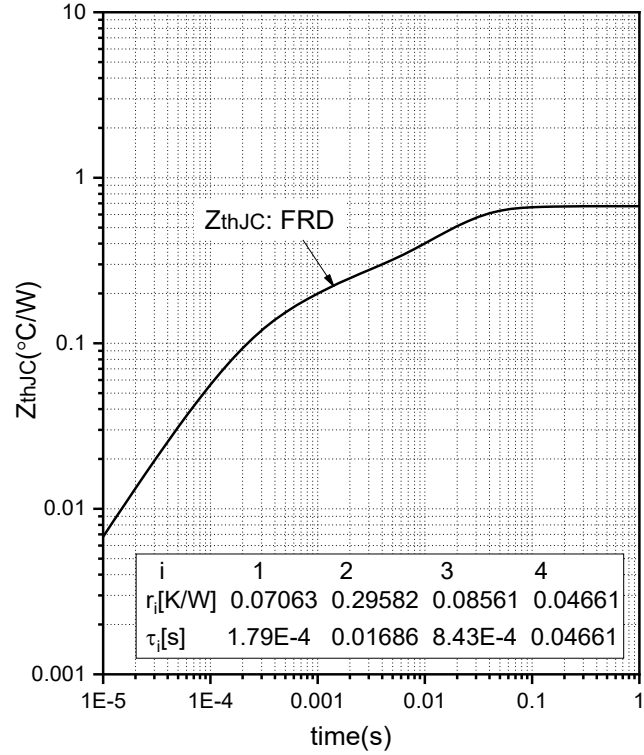


Fig.10 Transient Thermal Impedance (Diode)

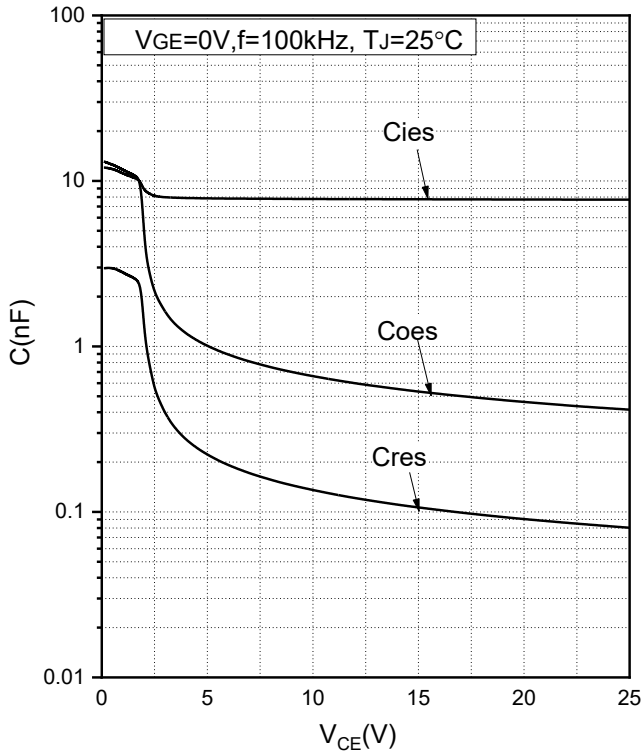


Fig.11 Capacitance Characteristics

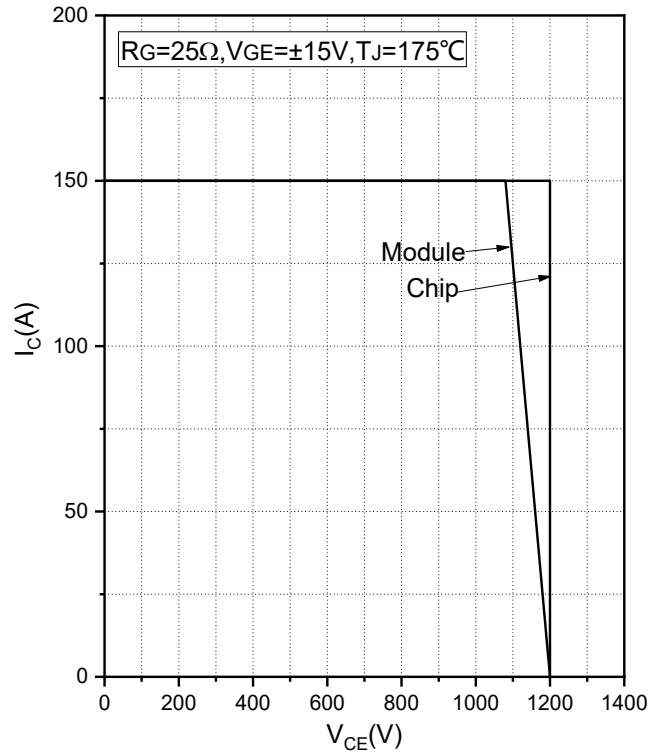


Fig.12 Reverse Bias Safe Operation Area (RBSOA)



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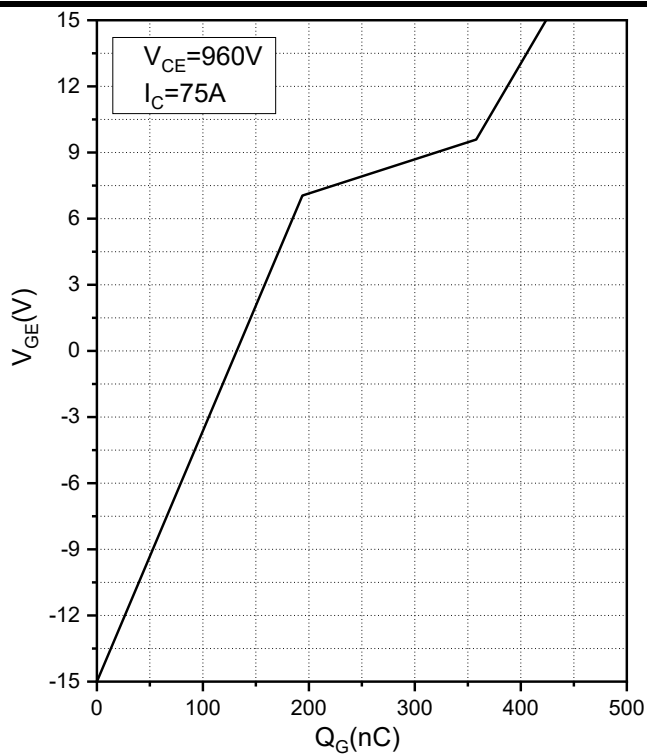


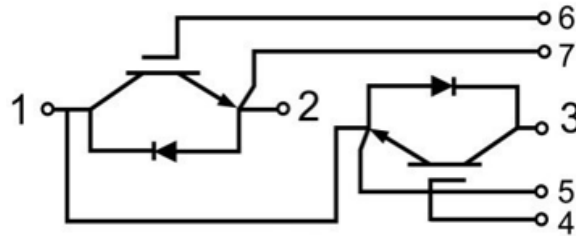
Fig.13 Gate Charge Characteristics



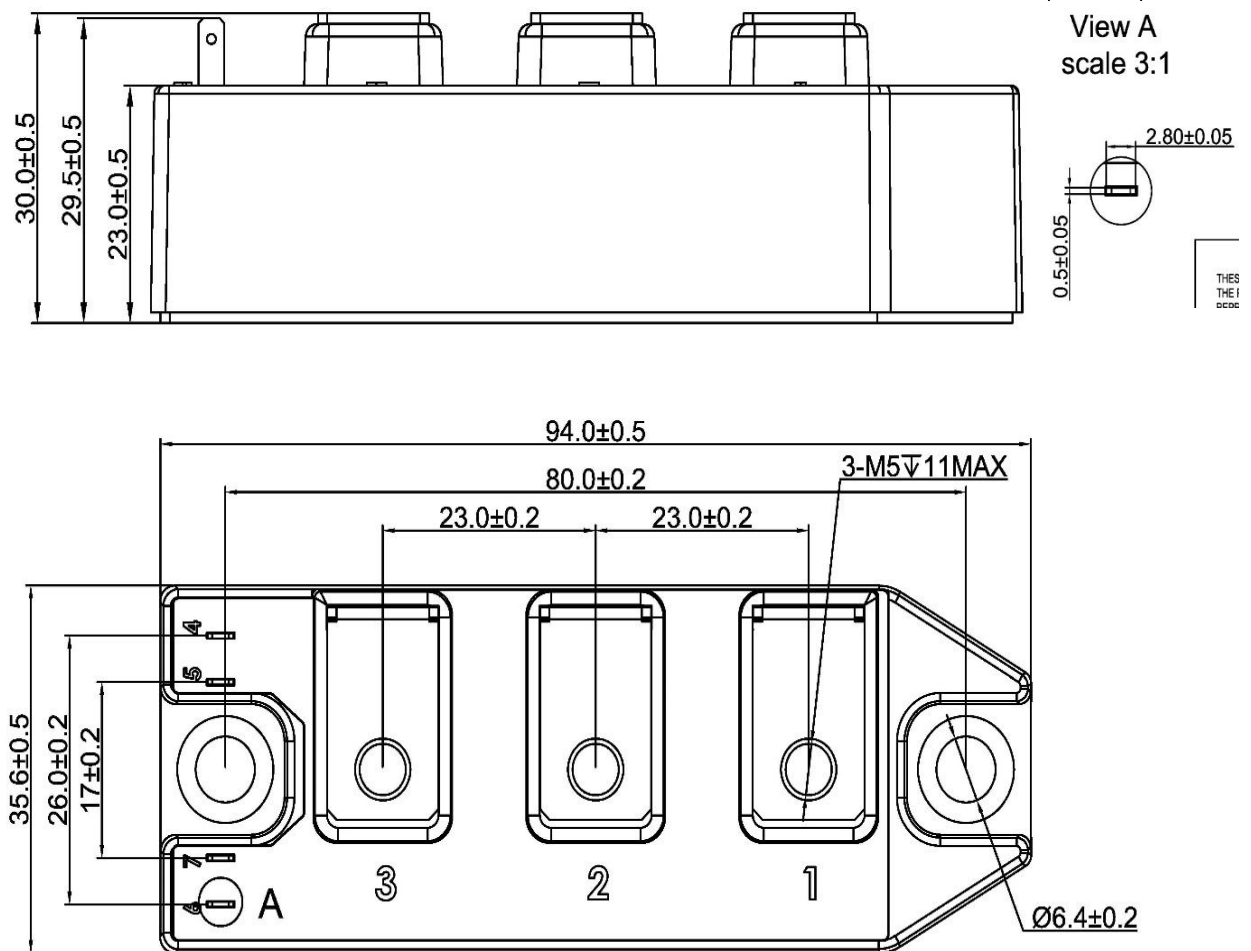
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Internal Circuit:



Package Outline (Unit: mm):



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Revision	Notes
A	Fina Datasheet Initial Release

Announcement

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